

MA3D756

Silicon epitaxial planar type (cathode common)

For switching power supply

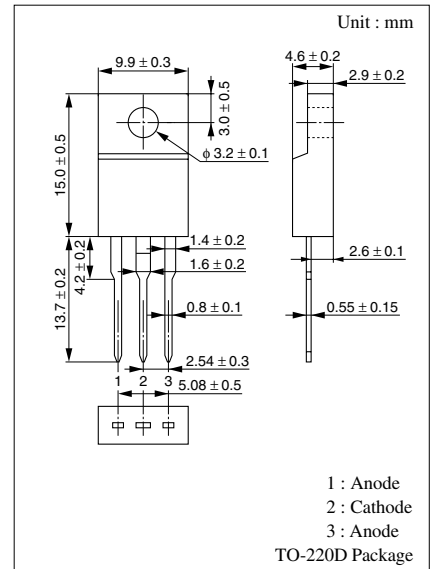
■ Features

- Low forward rise voltage V_F
- TO-220D (Full-pack package) with high dielectric breakdown voltage > 5.0 kV
- Easy-to-mount, caused by its V cut lead end

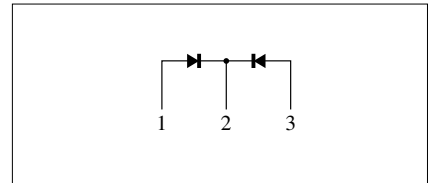
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	60	V
Average forward current	$I_{F(AV)}$	10	A
Non-repetitive peak forward surge current*	I_{FSM}	120	A
Junction temperature	T_j	-40 to +125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

Note) * : Half sine-wave; 10 ms/cycle



Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 60$ V			3	mA
Forward voltage (DC)	V_F	$I_F = 5$ A			0.58	V
Thermal resistance	$R_{th(j-c)}$	Direct current (between junction and case)			3	$^\circ\text{C/W}$

Note) Rated input/output frequency: 150 MHz

